



Complementary Enhancement Mode MOSFET - ESD Protected

Voltage

50 / -60V

Current

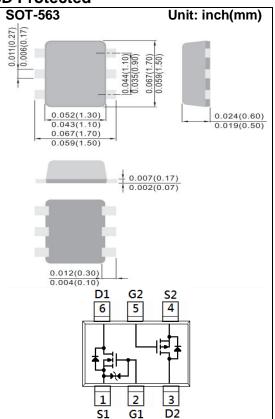
0.36A / -0.2A

Features

- Advanced Trench Process Technology
- Specially Designed for Switch Load, PWM Application, etc.
- ESD Protected 2KV HBM
- Lead free in compliance with EU RoHS 2011/65/EU directive
- Green molding compound as per IEC61249 Std. (Halogen Free)

Mechanical Data

- Case: SOT-563 Package
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.00009 ounces, 0.0026 grams
- Marking: X63



Maximum Ratings and Thermal Characteristics (T_A=25 °C unless otherwise noted)

| PARAMETER | SYMBOL | N-Ch LIMIT | P-Ch LIMIT | UNITS | |
|--|----------------------|-----------------|-------------|-------------|-------|
| Drain-Source Voltage | | V _{DS} | 50 | -60 | V |
| Gate-Source Voltage | | V_{GS} | <u>+</u> 20 | <u>+</u> 20 | V |
| Continuous Drain Current | | I _D | 360 | -200 | mA |
| Pulsed Drain Current (Note 4) | | I _{DM} | 1200 | -900 | mA |
| Barres Birata di a | T _a =25°C | <u></u> | 300 | | mW |
| Power Dissipation | Derate above 25°C | P _D | 2.4 | | mW/°C |
| Operating Junction and Storage Temperature Range | | T_J, T_{STG} | -55~150 | | °C |
| Typical Thermal resistance | | | | | |
| - Junction to Ambient (Note 3) | | $R_{\theta JA}$ | 417 | | °C/W |





N-Channel Electrical Characteristics (T_A=25 °C unless otherwise noted)

| PARAMETER | SYMBOL | TEST CONDITION | MIN. | TYP. | MAX. | UNITS |
|----------------------------------|---------------------|--|-----------|------|-------------|-------|
| Static | | 1201 00112111011 | 1 1111111 | 1 | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | V _{GS} =0V, I _D = 250uA | 50 | - | - | V |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS}=V_{GS}$, $I_{D}=250uA$ | 0.5 | 0.9 | 1.0 | V |
| Drain-Source On-State Resistance | R _{DS(on)} | V _{GS} = 10V, I _D = 500mA | - | 1.26 | 1.5 | Ω |
| | | V _{GS} = 4.5V, I _D = 200mA | - | 1.34 | 2.5 | |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{DS} = 50V, V _{GS} =0V | - | - | 1 | uA |
| Gate-Source Leakage Current | I _{GSS} | V _{GS} = <u>+</u> 20V, V _{DS} =0V | - | - | <u>+</u> 10 | uA |
| Dynamic (Note 5) | | | | | | |
| Total Gate Charge | Q_g | V _{DS} =25V, I _D =500mA, V _{GS} =4.5V | - | 0.95 | - | nC |
| Gate-Source Charge | Q_gs | | - | 0.34 | - | |
| Gate-Drain Charge | Q_{gd} | | - | 0.32 | - | |
| Input Capacitance | Ciss | V _{DS} =25V, V _{GS} =0V, f=1.0MHZ | - | 36 | - | pF |
| Output Capacitance | Coss | | - | 11 | - | |
| Reverse Transfer Capacitance | Crss | | - | 6.6 | - | |
| Turn-On Delay Time | td _(on) | \/ O5\/ 500 ·· A | - | 2.3 | - | |
| Turn-On Rise Time | tr | V_{DD} =25V, I_D =500mA, V_{GS} =10V, R_G =6 Ω (Note 1,2) | - | 20 | - | |
| Turn-Off Delay Time | td _(off) | | - | 7 | - | ns |
| Turn-Off Fall Time | tf | | - | 20 | - | |
| Drain-Source Diode | | | | | | |
| Maximum Continuous Drain-Source | | | | | 360 | m A |
| Diode Forward Current | I _S | | - | - | 360 | mA |
| Diode Forward Voltage | V_{SD} | I _S = 500mA, V _{GS} =0V | - | 0.9 | 1.5 | V |

NOTES:

- 1. Pulse width<a>300us, Duty cycle<a>2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. ROJA is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper.
- 4. The maximum current rating is package limited.
- 5. Guaranteed by design, not subject to production testing.





P-Channel Electrical Characteristics (T_A=25°C unless otherwise noted)

| PARAMETER | SYMBOL | TEST CONDITION | MIN. | TYP. | MAX. | UNITS |
|----------------------------------|---------------------|---|------|------|--------------|-------|
| Static | | | | | | |
| Drain-Source Breakdown Voltage | BV_{DSS} | V _{GS} =0V,I _D =-250uA | -60 | - | - | V |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS}=V_{GS}$, $I_{D}=-250uA$ | -1.0 | -1.5 | -2.5 | V |
| Drain-Source On-State Resistance | В | V _{GS} =-10V,I _D =-500mA | - | 2.6 | 6 | Ω |
| Diam-Source On-State Resistance | $R_{DS(on)}$ | V _{GS} =-4.5V,I _D =-200mA | - | 2.9 | 7 | |
| Zero Gate Voltage Drain Current | I_{DSS} | V_{DS} =-48V, V_{GS} =0V | - | - | -1 | uA |
| Gate-Source Leakage Current | I_{GSS} | V _{GS} = <u>+</u> 20V,V _{DS} =0V | - | - | <u>+</u> 100 | nA |
| Dynamic (Note 5) | | | | | | |
| Total Gate Charge | Q_g | V _{DS} =-25V, I _D =-100mA, V _{GS} =-4.5V | - | 1.1 | - | nC |
| Gate-Source Charge | Q_gs | | - | 0.3 | - | |
| Gate-Drain Charge | Q_gd | | - | 0.2 | - | |
| Input Capacitance | Ciss | V _{DS} =-25V, V _{GS} =0V, f=1.0MHZ | - | 51 | - | pF |
| Output Capacitance | Coss | | - | 15 | - | |
| Reverse Transfer Capacitance | Crss | | - | 2.2 | - | |
| Turn-On Delay Time | td _(on) | \\ O5\\ 400~A | - | 4.8 | - | |
| Turn-On Rise Time | tr | V_{DD} =-25V, I_{D} =-100mA, V_{GS} =-10V, R_{G} =6 Ω (Note 1.2) | - | 19 | - | ns |
| Turn-Off Delay Time | td _(off) | | - | 52 | - | |
| Turn-Off Fall Time | tf | K _G =012 | - | 32 | - | |
| Drain-Source Diode | | | | | | |
| Maximum Continuous Drain-Source | | | | | -200 | mA |
| Diode Forward Current | I _S | | - | - | -200 | |
| Diode Forward Voltage | V_{SD} | I _S =-500mA, V _{GS} =0V | - | -0.9 | -1.5 | V |





N-Channel TYPICAL CHARACTERISTIC CURVES

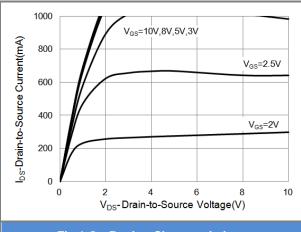


Fig.1 On-Region Characteristics

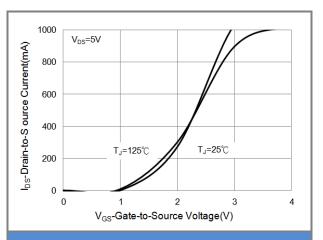


Fig.2 Transfer Characteristics

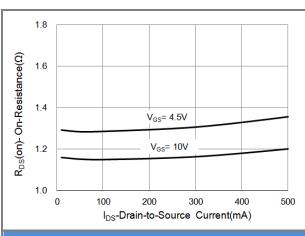


Fig.3 On-Resistance vs. Drain Current

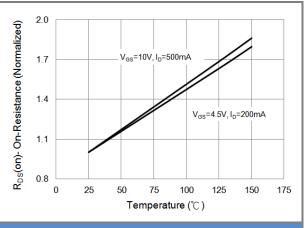


Fig.4 On-Resistance vs. Junction temperature

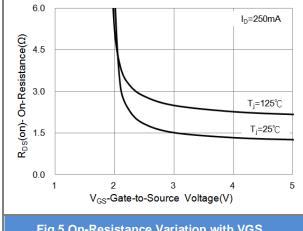


Fig.5 On-Resistance Variation with VGS.

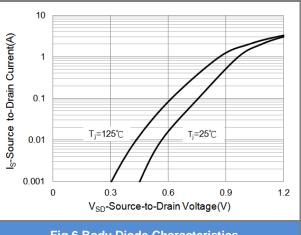


Fig.6 Body Diode Characteristics





N-Channel TYPICAL CHARACTERISTIC CURVES

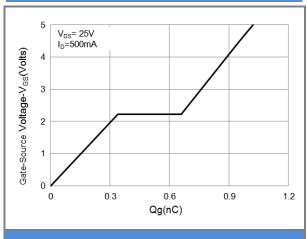


Fig.7 Gate-Charge Characteristics

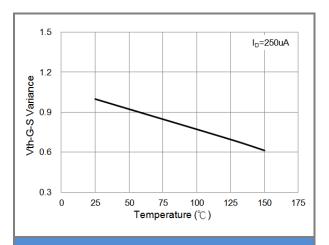


Fig.8 Threshold Voltage Variation with Temperature.

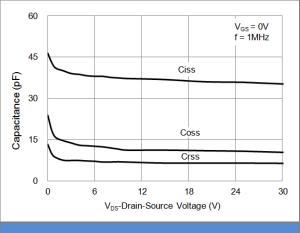


Fig.9 Capacitance vs. Drain-Source Voltage.





P-Channel TYPICAL CHARACTERISTIC CURVES

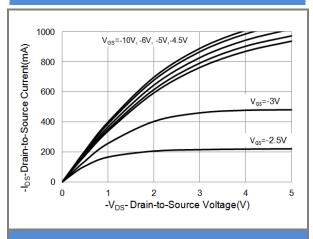


Fig.1 On-Region Characteristics

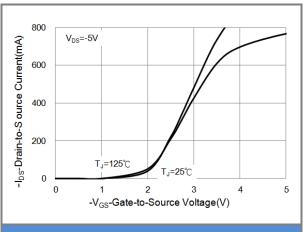


Fig.2 Transfer Characteristics

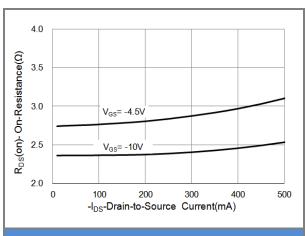


Fig.3 On-Resistance vs. Drain Current

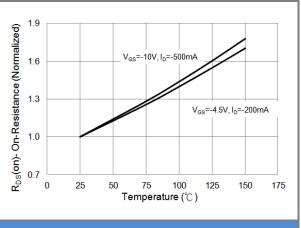


Fig.4 On-Resistance vs. Junction temperature

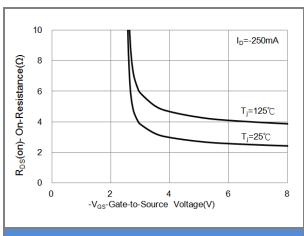


Fig.5 On-Resistance Variation with VGS.

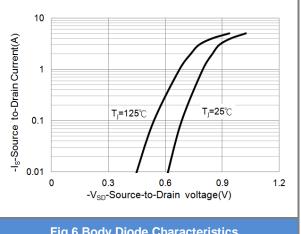


Fig.6 Body Diode Characteristics





P-Channel TYPICAL CHARACTERISTIC CURVES

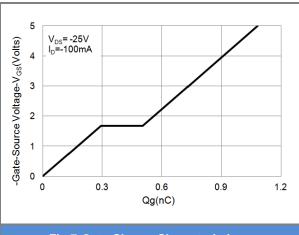


Fig.7 Gate-Charge Characteristics

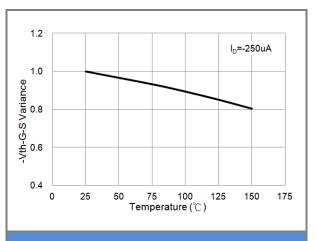


Fig.8 Threshold Voltage Variation with Temperature.

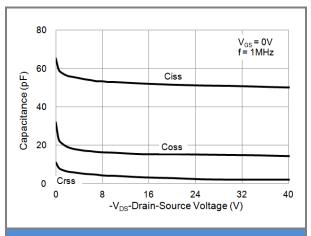


Fig.9 Threshold Voltage Variation with Temperature.

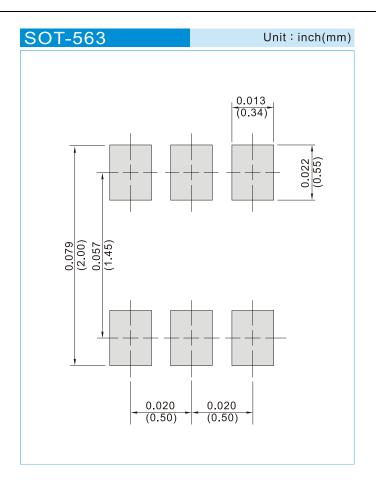




PART NO PACKING CODE VERSION

| Part No Packing Code | Package Type | Packing type | Marking | Version |
|----------------------|--------------|--------------------|---------|--------------|
| PJX8603_R1_00001 | SOT-563 | 4K pcs / 7" reel | X63 | Halogen free |
| PJX8603_R2_00001 | SOT-563 | 10K pcs / 13" reel | X63 | Halogen free |
| PJX8603_R1_00002 | SOT-563 | 8K pcs / 7" reel | X63 | Halogen free |
| PJX8603_R2_00002 | SOT-563 | 20K pcs / 13" reel | X63 | Halogen free |

MOUNTING PAD LAYOUT







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